



Titles

To view one or many selected titles scroll down the list and click the corresponding boxes. Then click display at the top of the page. To view one particular document click the link above the title to display immediately.

Documents 1 to 15 of 15 from your search "**strained ADJ silicon ADJ channel**" in all the available information:

Number of titles selected from other pages: 0

☐ **Select All**

☐ 1 [display full document](#)

2004. (INZZ) Two-dimensional quantum-mechanical modeling for **strained silicon channel** of double-gate MOSFET.

☐ 2 [display full document](#)

2005. (INZZ) Challenges and key potential technological innovations for scaling MOSFETS through the end of the roadmap.

☐ 3 [display full document](#)

2004. (INZZ) MOSFET scaling trends and challenges through the end of the roadmap.

☐ 4 [display full document](#)

2004. (INZZ) Average drift mobility and apparent sheet-electron density profiles in **strained-Si-SiGe buried-channel** depletion-mode n-MOSFETs.

☐ 5 [display full document](#)

2003. (INZZ) Nanometric electronics innovative architectures on thin **silicon** second lease of life for Moore's law?

☐ 6 [display full document](#)

2004. (INZZ) Secondary ion mass spectrometry characterization of source/drain junctions for **strained silicon channel** metal--oxide-semiconductor field-effect transistors.

☐ 7 [display full document](#)

2002. (INZZ) A 90 nm logic technology featuring 50 nm **strained silicon channel** transistors, 7 layers of Cu interconnects, low k ILD, and 1 mu m/sup 2 / SRAM cell.

☐ 8 [display full document](#)

2002. (INZZ) Advanced semiconductor technology for system-on-chip (SOC).

☐ 9 [display full document](#)

2001. (INZZ) Impact of **strained-Si channel** on complementary metal oxide semiconductor circuit performance under the sub-100 nm regime.

☐ 10 [display full document](#)

2000. (INZZ) Novel **strained-Si** heterostructure NMOSFETs on solid phase epitaxially grown relaxed Si/sub 1-x/Ge/sub x/.

☐ 11 [display full document](#)

1999. (INZZ) SiGe virtual substrate **N-channel** heterojunction MOSFETs.

☐ 12 [display full document](#)

1998. (INZZ) Monte Carlo investigation of optimal device architectures for SiGe FETs.

☐ 13 [display full document](#)

1998. (INZZ) Far-infrared cyclotron resonance study of the effect of strain and localisation in Si/SiGe two dimensional electron gases.

☐ 14 [display full document](#)

1995. (INZZ) High speed deep sub-micron MOSFET using high mobility **strained silicon channel**.

☐ 15 [display full document](#)

1995. (INZZ) Monte Carlo simulation of electron transport in **strained** Si/Si/sub 1-x /Ge/sub x/ n-MOSFETs.

Selection	Display Format	Output Format	ERA SM Electronic Redistribution & Archiving
<input checked="" type="radio"/> from this page <input type="radio"/> from all pages	<input checked="" type="radio"/> Full <input type="radio"/> Free <input type="radio"/> Short <input type="radio"/> Medium <input type="radio"/> Custom Help with Formats	<input checked="" type="radio"/> HTML <input type="radio"/> Tagged (for tables) <input type="radio"/> PDF <input type="radio"/> RTF	Copies you will redistribute: <input type="text"/> Employees who will access archived record (s): <input type="text"/> Help with ERA
Sort your entire search result by <input type="text" value="Publication year"/> <input type="button" value="Ascending"/>			

Top - News & FAQs - Dialog

© 2005 Dialog


[options](#)
[logoff](#)
[feedback](#)
[help](#)
[databases](#)
[search page](#)

Titles

To view one or many selected titles scroll down the list and click the corresponding boxes. Then click display at the bottom of the page. To view one particular document click the link above the title to display immediately.

Documents 1 to 2 of 2 from your search "**strained ADJ si ADJ source**" in all the available information:
Number of titles selected from other pages: 0

☐ **Select All**
☐ 1 [display full document](#)

2003. (INZZ) CMOS Front-End Materials and Process Technology. Symposium (Mater. Res. Soc. Symposium Proceedings Vol. 765).

☐ 2 [display full document](#)

1999. (INZZ) Effect of the Ge-molefraction on the subthreshold slope and leakage current of vertical Si/Si/sub 1-x/Ge/sub x/ MOSFETs.

Selection	Display Format	Output Format	ERA SM Electronic Redistribution & Archiving
<input checked="" type="radio"/> from this page <input type="radio"/> from all pages	<input checked="" type="radio"/> Full <input type="radio"/> Free <input type="radio"/> Short <input type="radio"/> Medium <input type="radio"/> Custom Help with Formats	<input checked="" type="radio"/> HTML <input type="radio"/> Tagged (for tables) <input type="radio"/> PDF <input type="radio"/> RTF	Copies you will redistribute: <input type="text"/> Employees who will access archived record (s): <input type="text"/> Help with ERA
<div> Sort your entire search result by <div> Publication year <div></div> </div> Ascending </div>			

[options](#)[logout](#)[feedback](#)[help](#)[databases](#)[easy
search](#)

Advanced Search:

INSPEC - 1969 to date (INZZ)

[limit](#)

Search history:

No.	Database	Search term	Info added since	Results	
1	INZZ	SMOS AND strained	unrestricted	0	-
2	INZZ	strained ADJ silicon ADJ channel	unrestricted	15	show titles
3	INZZ	strained ADJ silicon ADJ source	unrestricted	0	-
4	INZZ	strained ADJ silicon ADJ drain	unrestricted	0	-
5	INZZ	strained ADJ germanium ADJ source	unrestricted	0	-
6	INZZ	strained ADJ germanium ADJ drain	unrestricted	0	-
7	INZZ	strained ADJ si ADJ source	unrestricted	2	show titles
8	INZZ	strained ADJ si ADJ drain	unrestricted	0	-

[hide](#) | [delete all search steps...](#) | [delete individual search steps...](#)Enter your search term(s): [Search tips](#) ☐ Thesaurus mapping Information added since: or:
(YYYYMMDD)[search](#)

Select special search terms from the following list(s):

- ☒ Publication year
- ☒ Classification codes A: Physics, 0-1
- ☒ Classification codes A: Physics, 2-3
- ☒ Classification codes A: Physics, 4-5
- ☒ Classification codes A: Physics, 6
- ☒ Classification codes A: Physics, 7
- ☒ Classification codes A: Physics, 8
- ☒ Classification codes A: Physics, 9
- ☒ Classification codes B: Electrical & Electronics, 0-5